

**N-Channel Power MOSFET** 

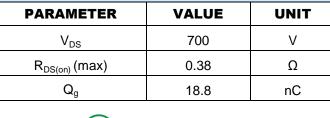
700V, 11A, 0.38Ω

#### **FEATURES**

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

## **APPLICATION**

- Power Supply
- Lighting



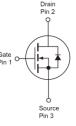
**KEY PERFORMANCE PARAMETERS** 











Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (D-PAK) per J-STD-020

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25°C unless otherwise noted)					
PARAMETER	SYMBOL	ITO-220	IPAK/DPAK	UNIT	
Drain-Source Voltage		$V_{\text{DS}}$	7	V	
Gate-Source Voltage		$V_{GS}$	Ę	V	
Continuous Drain Current (Note 1)	$T_c = 25^{\circ}C$			A	
Continuous Drain Current	$T_{\rm C} = 100^{\circ}{\rm C}$		(		
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	:	А	
Total Power Dissipation @ $T_C = 25^{\circ}C$		P <sub>DTOT</sub>	33 125		W
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	156		mJ
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	2.5		А
Operating Junction and Storage Temperature Range		$T_J, T_STG$	- 55 t	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	ITO-220	IPAK/DPAK	UNIT	
Junction to Case Thermal Resistance	R <sub>ejc</sub>	3.8	1	°C/W	
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>		62	°C/W	

Notes: R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R<sub>OJA</sub> is guaranteed by design while R<sub>OCA</sub> is determined by the user's board design. R<sub>0JA</sub> shown below for single device operation on FR-4 PCB in still air.





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<b>ELECTRICAL SPECIFICATIONS</b> ( $T_A = 25^{\circ}C$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)	·			•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250 \mu A$	BV <sub>DSS</sub>	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30 \text{V},  V_{DS} = 0 \text{V}$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700 V, V_{GS} = 0 V$	I <sub>DSS</sub>			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 3.3A$	R <sub>DS(on)</sub>		0.33	0.38	Ω
Dynamic <sup>(Note 5)</sup>	·			•		
Total Gate Charge	$V_{DS} = 380V, I_{D} = 11A,$	Qg		18.8		 nC 
Gate-Source Charge		Q <sub>gs</sub>		3.7		
Gate-Drain Charge	V <sub>GS</sub> = 10V	Q <sub>gd</sub>		5.6		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		981		_
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		58		pF
Gate Resistance	F = 1MHz, open drain	R <sub>g</sub>		3.3		Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 35\Omega,$ $I_{D} = 11A, V_{GS} = 10V,$	t <sub>d(on)</sub>		32		
Turn-On Rise Time		t <sub>r</sub>		21		
Turn-Off Delay Time		t <sub>d(off)</sub>		62		ns
Turn-Off Fall Time		t <sub>f</sub>		28		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_{S} = 11A, V_{GS} = 0V$	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	V <sub>R</sub> =200V, I <sub>S</sub> = 5.5A	t <sub>rr</sub>		226		ns
Reverse Recovery Charge	dl <sub>F</sub> /dt = 100A/µs	Q <sub>rr</sub>		2.1		μC

#### Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 50mH, I\_{AS} = 2.5A, V\_{DD} = 50V, R\_G = 25\Omega, Starting T\_J =  $25^{\circ}C$ 

4. Pulse test: PW  $\leq$  300µs, duty cycle  $\leq$  2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



## **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM70N380CI C0G	ITO-220	50pcs / Tube
TSM70N380CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N380CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

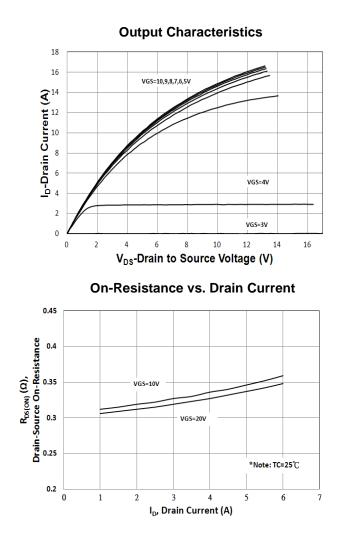
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

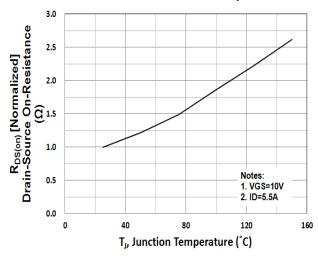


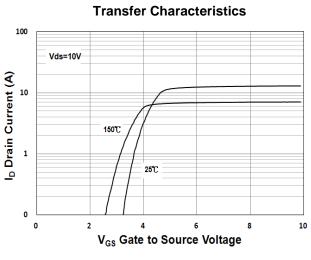
# **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

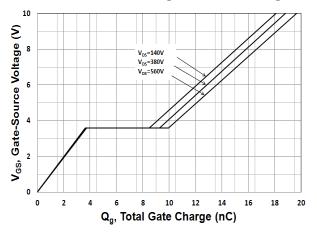


**On-Resistance vs. Junction Temperature** 

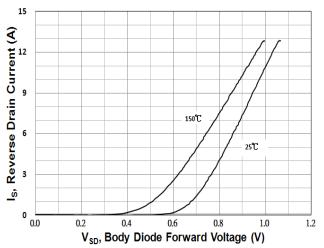




Gate-Source Voltage vs. Gate Charge



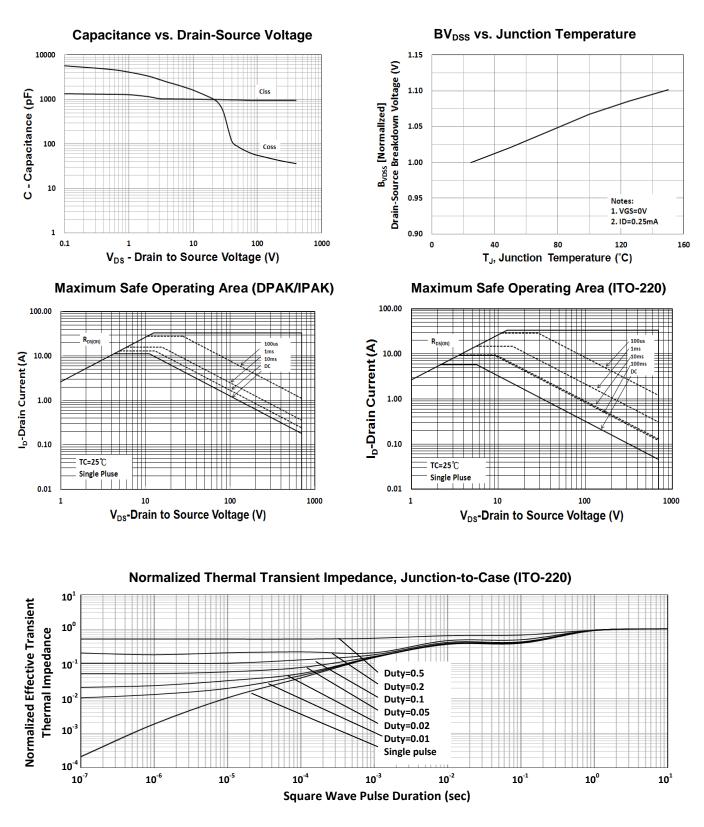
Source-Drain Diode Forward Current vs. Voltage





# **CHARACTERISTICS CURVES**

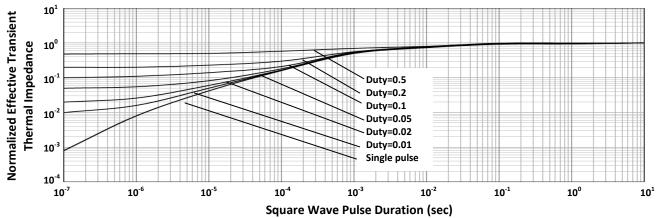
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 





# **ELECTRICAL CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 



# Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)

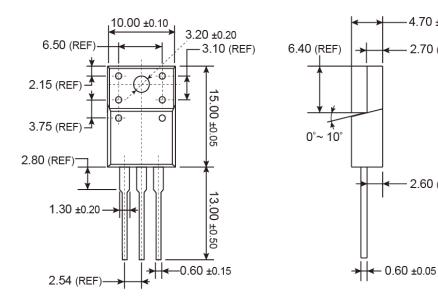


4.70 ±0.10

2.70 (REF)

2.60 (REF)

# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



#### **MARKING DIAGRAM**

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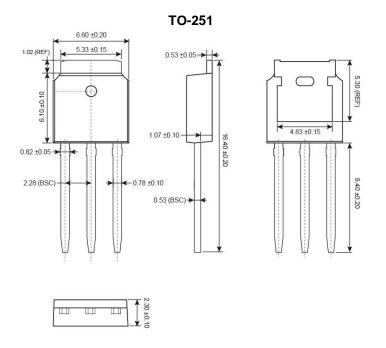


- **G** = Halogen Free
- Y = Year Code
- **WW** = Week Code (01~52)
  - **F** = Factory Code

#### ITO-220



# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



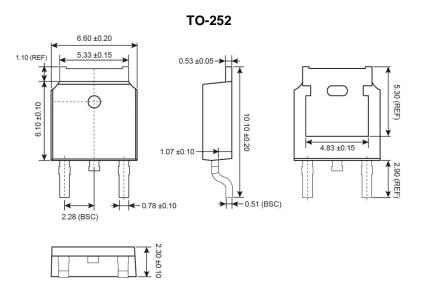
## **MARKING DIAGRAM**

5	-	= Year Code = Month Code	e for	Haloge	en Fr	ee Proo	duct	
70N380 YML		O =Jan S =May						•
	L	W =Sep = Lot Code (1	Х	=Oct				•
#1		, ,	·	,				

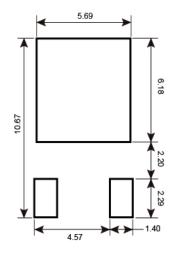




# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



## SUGGESTED PAD LAYOUT (Unit: Millimeters)



### **MARKING DIAGRAM**

$\square$	Y = Year Code
5	M = Month Code for Halogen Free Product
70N380	<b>O</b> =Jan <b>P</b> =Feb <b>Q</b> =Mar <b>R</b> =Apr
YML	<b>S</b> =May <b>T</b> =Jun <b>U</b> =Jul <b>V</b> =Aug
() <sup>[]</sup> ()	W =Sep X =Oct Y =Nov Z =Dec
#1∐ ∐	L = Lot Code (1~9, A~Z)



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